The PETsys High Performance TOFPET2 ASIC is a new 64 channel chip for the readout and digitization of signals from fast photon detectors in applications where a high data rate and fast timing is required. Fig. 1 shows a simplified block diagram of the ASIC.

Each of the 64 channels has a front-end current conveyor followed by two post amplifiers, one for the time branch and one for the energy branch. The time branch uses a low threshold (t1) for timing and a second threshold (t2) for rejecting dark counts, avoiding deadtime. The energy branch has a higher threshold (tE) for validating the event. The t1 threshold will typically be set at a value corresponding to a few photons. Only events that also pass the energy threshold are digitised. All thresholds are separately configurable for each channel.

There are four Time to Amplitude Converters (TAC) in the timing branch and four Charge Integrators (CI) in the energy branch, allowing a high event rate with negligible dead-time. The charge integration time is configurable up to one microsecond.

The energy of the event can also be obtained from Time Over Threshold (TOT) by using four additional TACs instead of the CIs in the energy branch. When charge integration is selected, ToT is available with clock period resolution. There are two 10-bit Wilkinson ADCs per channel, one for the time branch and one for the energy branch.

Each channel has an embedded counter, incremented each time a signal triggers the low threshold t1. This provides a dark count counter for SiPM characterisation.

The ASIC is available as BGA package (fig. 2). We also provide the complete solution for reading a few 100, a few 1000 or several 10'000 channels. In this readout the ASIC is mounted on the FEB/A board (fig. 3).

A more extensive performance report is available in reference [1], and a full data sheet is available on our web site.

Main features of the PETsys TOFPET2 ASIC.

- Designed in standard CMOS 110 nm technology.
- Signal amplification and discrimination for each of 64 independent channels.
- Separately configurable t1, t2 and energy thresholds for each channel.
- Rejects dark counts without triggering, allowing to handle large dark counts rates.
- Configurable charge integration time up to one microsecond.
- Quad-buffered TDCs and charge integrators for each channel. The first branch is used for timing measurement. The second branch can either be used for time-over-threshold (ToT) or charge measurement with a Wilkinson ADC.
- Dynamic range: 1500 pC.
- TDC time binning: 30 ps.
- Gain adjustment per channel in the charge branch: 1, 1/2, 1/4, 1/8.
- On-chip charge calibration pulse generator with 6-bit programmable amplitude.
- Main clock frequency: 160-200 MHz.
- Configurable digital data output over 1, 2, or 4 LVDS data links at 2x the main clock frequency and single data rate (SDR) or double data rate (DDR).
- Max output data rate per ASIC: 3.2 Gb/s.
- Max event rate per channel: 600 kevents, 80 bits per event.
- Power dissipation per channel: 8.2 mW, for the recommended settings.
**Dark Counts.**
Dark count as a function of threshold DAC setting. This measurement was performed with a KETEK-PM3325-WB SiPM at 4 V over-voltage and at 20 °C.

**Energy spectrum.**
Pulse height spectrum obtained with a radioactive source of $^{22}\text{Na}$ and with a LYSO crystal of 3x3x5 mm³ mounted on a KETEK-PM3325-WB SiPM at 4 V over-voltage and at 20 °C. The charge signal is integrated in a time window of 350 ns. The energy resolution at 511 keV is 10.5 %. The energy spectrum is corrected for the non-linearity of the SiPM by recording pulse height spectra with $^{133}\text{Ba}$, $^{22}\text{Na}$ and $^{137}\text{Cs}$ sources and fitting the relation between ADC counts and gamma energy for the different gamma emissions lines.

**Coincidence Time Resolution.**
CTR measured with a $^{22}\text{Na}$ point source and two Hamamatsu S13361-3050AE-04 MPPC arrays. This MPPC array has pixels measuring 3x3 mm with 50 μm cells. Left figure: CTR measured with two 3x3x20 mm³ LYSO crystals at 15 °C, 4 V over-voltage. Right figure: measured with two 2x2x3 mm³ LYSO crystals at 15 °C, 3 V over-voltage. The LYSO:Ce crystals used in these measurements were obtained from CPI.